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Attorney's Docket No.: 07977-010005 / US2941D1D1D1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	: Naoto Kusumoto, et al.	Art Unit	: 2814
Serial No.	: 09/941,367	Examiner	: Theresa T. Doan
Filed	: August 28, 2001		
Title	: METHOD FOR PRODUCING INSULATED GATE THIN FILM SEMICONDUCTOR DEVICE		

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

TRANSMITTAL LETTER

Correspondence relating to this application is enclosed. The required fees are computed below. Please apply any charges not covered, or any credits, to Deposit Account No. 06-1050.

Total Claims	60	-	108	=	0	$0
Independent	23	-	23	=	0	$0
First Presentation of Multiple Dependent Claims						$0
Applicant hereby petitions under 37 C.F.R. §1.136 for a 0 month extension of time.						$0
TOTAL FEE DUE						$0

Respectfully submitted,

Date: 2/03/2005

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Applicant	: Kusumoto, et al.	Art Unit	: 2814
Serial No.	: 09/941,367	Examiner	: Theresa T. Doan
Filed	: August 28, 2001	Confirmation No.: 9944	
Title	: METHOD FOR PRODUCING INSULATED GATE THIN FILM SEMICONDUCTOR DEVICE		

MAIL STOP AF
Commissioner for Patents
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REPLY TO ACTION OF NOVEMBER 3, 2004

In reply to the Final Office Action of November 3, 2004, Applicants submit the following remarks.

Claims 1-30 are pending, with claims 1, 2, 9, and 10 being independent. Claims 3-8, 11-16, and 21-30 were withdrawn from consideration due to a previous restriction requirement, and claims 1, 2, 9, 10, and 17-20 have been examined.

Claims 1, 2, 9, 10, and 17-20 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Applicants' Prior Art (APA) in view of Asano (5,409,867) and further in view of Miyao (4,599,133). Applicants respectfully traverse this rejection.

Independent claims 1, 2, and 10 recite a method for manufacturing a semiconductor device having at least one thin film transistor that includes, among other features, irradiating the semiconductor layer with a laser beam to crystallize a semiconductor layer, where the irradiation of the semiconductor layer is conducted in such a manner that the semiconductor layer is scanned with the laser beam in parallel with a carrier flow direction in the channel region.

Applicants respectfully request reconsideration and withdrawal of the rejection of claims 1, 2, and 10, and their dependent claims, because APA, Asano, and Miyao, either alone in combination, fail to describe or suggest irradiating the semiconductor layer with a laser beam to crystallize a semiconductor layer in such a manner that there is a relationship between the irradiating direction and the carrier flow direction. More specifically, the references fail to describe or suggest irradiating the semiconductor layer in such a manner that the semiconductor